

**TC74ACT573P, TC74ACT573F, TC74ACT573FW, TC74ACT573FT****OCTAL D-TYPE LATCH WITH 3-STATE OUTPUT**

The TC74ACT573 is an advanced high speed CMOS OCTAL LATCH fabricated with silicon gate and double-layer metal wiring C<sup>2</sup>MOS technology.

It achieves the high speed operation similar to equivalent Bipolar Schottky TTL while maintaining the CMOS low power dissipation.

This device may be used as a level converter for interfacing TTL or NMOS to High Speed CMOS. The inputs are compatible with TTL, NMOS and CMOS output voltage levels. These 8-bit D-type latches are controlled by a latch enable (LE) and a output enable input ( $\overline{OE}$ ).

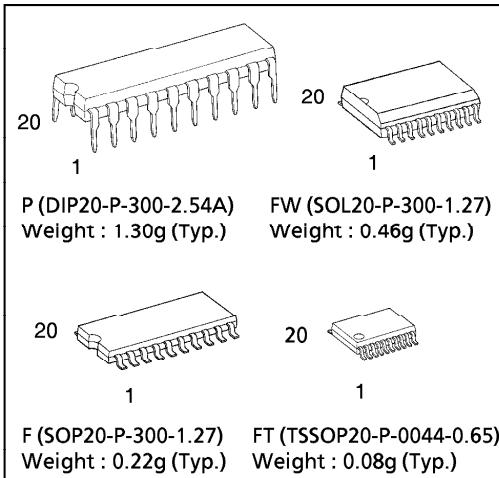
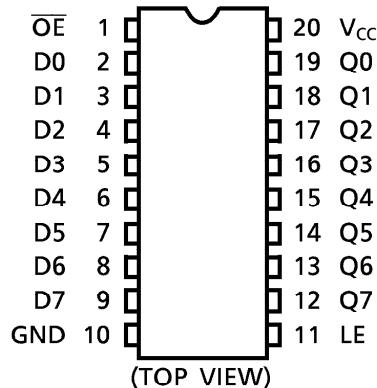
When the  $\overline{OE}$  input is high, the eight outputs are in a high impedance state.

All inputs are equipped with protection circuits against static discharge or transient excess voltage.

**FEATURES :**

- High Speed..... $t_{pd} = 5.5\text{ns}$  (typ.) at  $V_{CC} = 5\text{V}$
- Low Power Dissipation..... $I_{CC} = 8\mu\text{A}$ (Max.) at  $T_a = 25^\circ\text{C}$
- Compatible with TTL outputs.... $V_{IL} = 0.8\text{V}$  (Max.)  
 $V_{IH} = 2.0\text{V}$  (Min.)
- Symmetrical Output Impedance... $|I_{OH}| = I_{OL} = 24\text{mA}$  (Min.)  
Capability of driving  $50\Omega$  transmission lines.
- Balanced Propagation Delays..... $t_{PLH} \approx t_{PHL}$
- Pin and Function Compatible with 74F573

(Note) The JEDEC SOP (FW) is not available in Japan.

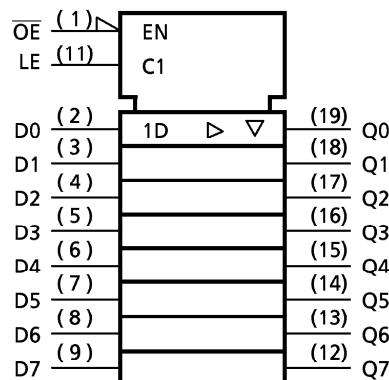
**PIN ASSIGNMENT****TRUTH TABLE**

INPUTS			OUTPUTS
$\overline{OE}$	LE	D	Q
H	X	X	Z
L	L	X	$Q_n$
L	H	L	L
L	H	H	H

X : Don't Care

Z : High Impedance

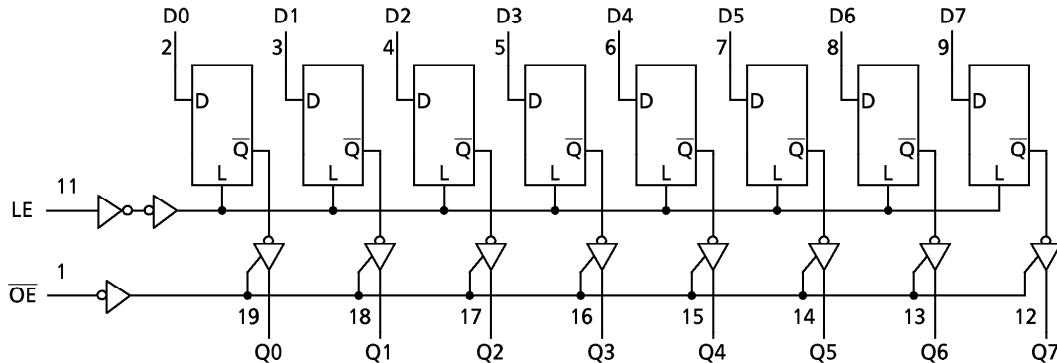
$Q_n$  : Q outputs are latched at the time when the LE input is taken to a low logic level.

**IEC LOGIC SYMBOL**

961001EBA2

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## SYSTEM DIAGRAM



## ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage Range	$V_{CC}$	-0.5~7.0	V
DC Input Voltage	$V_{IN}$	-0.5~ $V_{CC} + 0.5$	V
DC Output Voltage	$V_{OUT}$	-0.5~ $V_{CC} + 0.5$	V
Input Diode Current	$I_{IK}$	$\pm 20$	mA
Output Diode Current	$I_{OK}$	$\pm 50$	mA
DC Output Current	$I_{OUT}$	$\pm 50$	mA
DC $V_{CC}$ /Ground Current	$I_{CC}$	$\pm 200$	mA
Power Dissipation	$P_D$	500 (DIP)* / 180 (SOP/TSSOP)	mW
Storage Temperature	$T_{stg}$	-65~150	°C

\*500mW in the range of  $T_a = -40^{\circ}\text{C} \sim 65^{\circ}\text{C}$ . From  $T_a = 65^{\circ}\text{C}$  to  $85^{\circ}\text{C}$  a derating factor of  $-10\text{mW}/^{\circ}\text{C}$  should be applied up to 300mW.

## RECOMMENDED OPERATING CONDITIONS

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage	$V_{CC}$	4.5~5.5	V
Input Voltage	$V_{IN}$	0~ $V_{CC}$	V
Output Voltage	$V_{OUT}$	0~ $V_{CC}$	V
Operating Temperature	$T_{opr}$	-40~85	°C
Input Rise and Fall Time	$dt / dV$	0~10	ns / V

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## DC ELECTRICAL CHARACTERISTICS

PARAMETER	SYMBOL	TEST CONDITION	$V_{CC}$ (V)	Ta = 25°C			Ta = -40~85°C		UNIT
				MIN.	TYP.	MAX.	MIN.	MAX.	
High - Level Input Voltage	$V_{IH}$		4.5 5.5	2.0	—	—	2.0	—	V
Low - Level Input Voltage	$V_{IL}$		4.5 5.5	—	—	0.8	—	0.8	V
High - Level Output Voltage	$V_{OH}$	$V_{IN} = V_{IH}$ or $V_{IL}$	$I_{OH} = -50\mu A$ $I_{OH} = -24mA$ $I_{OH} = -75mA^*$	4.5 4.5 5.5	4.4 3.94 —	4.5 — —	—	4.4 3.80 3.85	— — —
Low - Level Output Voltage	$V_{OL}$	$V_{IN} = V_{IH}$ or $V_{IL}$	$I_{OL} = 50\mu A$ $I_{OL} = 24mA$ $I_{OL} = 75mA^*$	4.5 4.5 5.5	— — —	0.0 0.1 0.36	— — —	0.1 0.44 1.65	V
3 - State Output Off - State Current	$I_{OZ}$	$V_{IN} = V_{IH}$ or $V_{IL}$ $V_{OUT} = V_{CC}$ or GND	5.5	—	—	$\pm 0.5$	—	$\pm 5.0$	$\mu A$
Input Leakage Current	$I_{IN}$	$V_{IN} = V_{CC}$ or GND	5.5	—	—	$\pm 0.1$	—	$\pm 1.0$	
Quiescent Supply Current	$I_{CC}$	$V_{IN} = V_{CC}$ or GND	5.5	—	—	8.0	—	80.0	
	$I_C$	PER INPUT : $V_{IN} = 3.4V$ OTHER INPUT : $V_{CC}$ or GND	5.5	—	—	1.35	—	1.5	mA

\* : This spec indicates the capability of driving 50Ω transmission lines.

One output should be tested at a time for a 10ms maximum duration.

TIMING REQUIREMENTS (Input  $t_r = t_f = 3ns$ )

PARAMETER	SYMBOL	TEST CONDITION	Ta = 25°C		Ta = -40~85°C		UNIT
			$V_{CC}$ (V)	LIMIT	LIMIT	LIMIT	
Minimum Pulse Width (LE)	$t_W(H)$		5.0 ± 0.5	5.0	5.0	5.0	ns
Minimum Set - up Time	$t_s$		5.0 ± 0.5	3.0	3.0	3.0	
Minimum Hold Time	$t_h$		5.0 ± 0.5	2.0	2.0	2.0	

AC ELECTRICAL CHARACTERISTICS ( $C_L = 50\text{pF}$ ,  $R_L = 500\Omega$ , Input  $t_r = t_f = 3\text{ns}$ )

PARAMETER	SYMBOL	TEST CONDITION	Ta = 25°C			Ta = -40~85°C		UNIT
			V <sub>CC</sub> (V)	MIN.	TYP.	MAX.	MIN.	
Propagation Delay Time ( LE-Q )	$t_{pLH}$ $t_{pHL}$		5.0 ± 0.5	—	6.3	10.5	1.0	12.0
Propagation Delay Time ( Dn-Q )	$t_{pLH}$ $t_{pHL}$		5.0 ± 0.5	—	6.2	9.6	1.0	11.0
Output Enable Time	$t_{pZL}$ $t_{pZH}$		5.0 ± 0.5	—	6.5	10.0	1.0	11.5
Output Disable Time	$t_{pLZ}$ $t_{pHZ}$		5.0 ± 0.5	—	6.5	8.8	1.0	10.0
Input Capacitance	C <sub>IN</sub>		—	5	10	—	10	pF
Output Capacitance	C <sub>OUT</sub>		—	10	—	—	—	
Power Dissipation Capacitance	C <sub>PD</sub> (1)		—	22	—	—	—	

Note (1) C<sub>PD</sub> is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation :

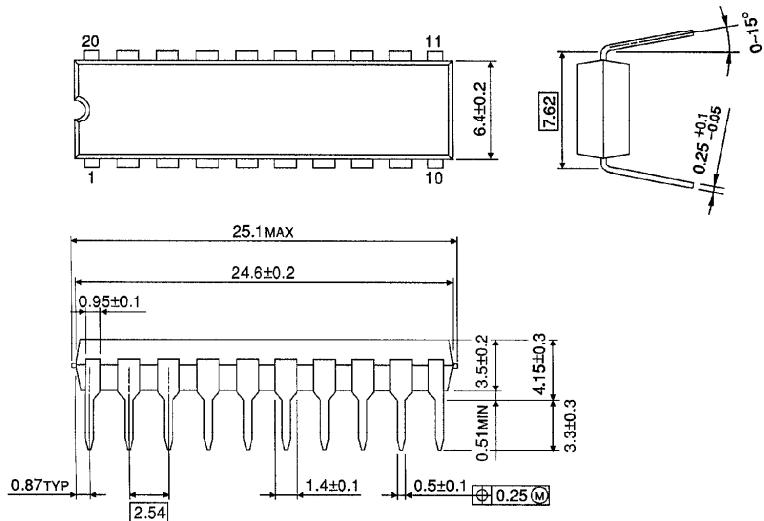
$$I_{CC}(\text{opr.}) = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/8 \text{ (per Latch)}$$

And the total C<sub>PD</sub> when n pcs. of Latch operate can be gained by the following equation:

$$C_{PD}(\text{total}) = 6 + 16 \cdot n$$

## DIP 20PIN OUTLINE DRAWING (DIP20-P-300-2.54A)

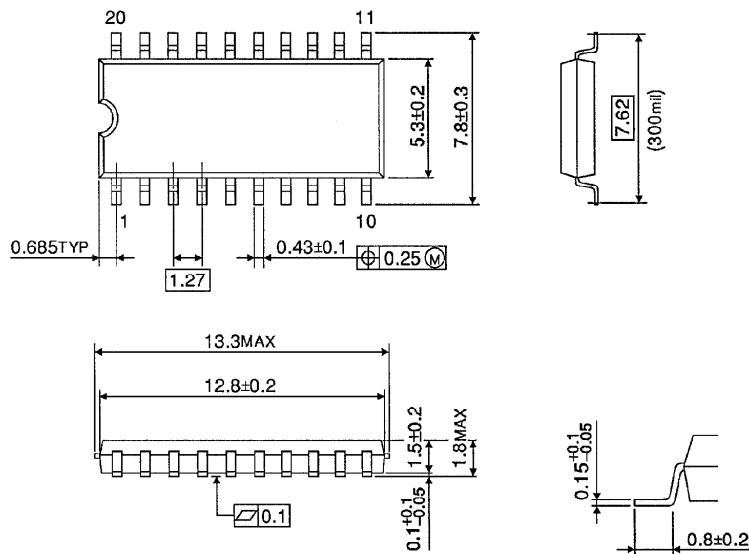
Unit in mm



Weight : 1.30g (Typ.)

## SOP 20PIN (200mil BODY) OUTLINE DRAWING (SOP20-P-300-1.27)

Unit in mm

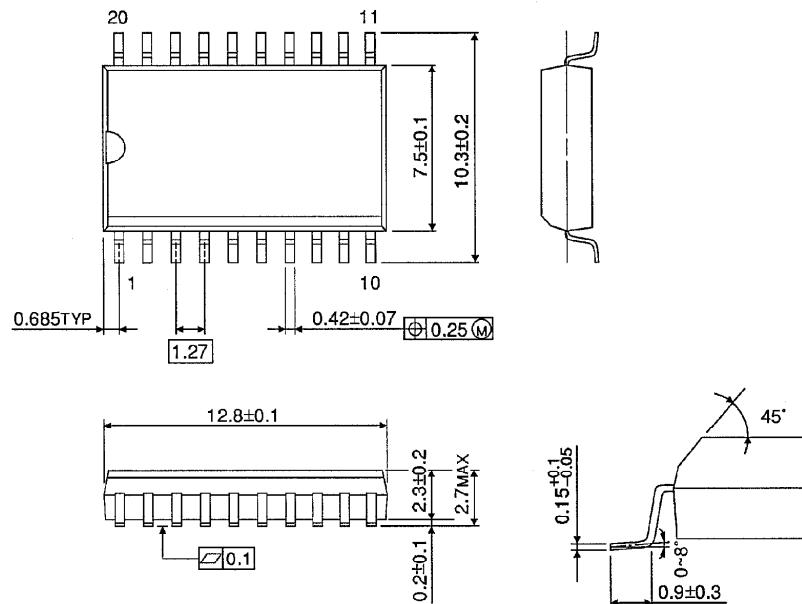


Weight : 0.22g (Typ.)

## SOP 20PIN (300mil BODY) OUTLINE DRAWING (SOL20-P-300-1.27)

Unit in mm

(Note) This package is not available in Japan.



## TSSOP 20PIN OUTLINE DRAWING (TSSOP20-P-0044-0.65)

Unit in mm

